

ABSOLUTE MAXIMUM RATINGS AT T_A=25

PARAMETER	MAXIMUM RATING	UNIT
IR Diode Continuous Forward Current	60	mA
IR Diode Reverse Voltage	5	V
Transistor Collector Current	20	mA
Transistor Power Dissipation	75	mW
IR Diode Peak Forward Current (Pulse Wide = 10 μ S, 300 pps)	1	A
Diode Power Dissipation	100	mW
Phototransistor Collector-Emitter Voltage	30	V
Phototransistor Emitter-Collector Voltage	5	V
Operating Temperature Range	-25 to + 85	
Storage Temperature Range	-40 to + 100	
Lead Soldering Temperature [1.6mm(.063") From Case]	260 for 5 Seconds	

ELECTRICAL OPTICAL CHARACTERISTICS AT TA=25

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
INPUT LED						
Forward Voltage	V _F		1.2	1.6	V	I _F = 20mA
Reverse Current	I _R			100	μ A	V _R =5V
OUTPUT PHOTOTRANSISTOR						
Collector-Emitter Breakdown Voltage	V(BR) _{CEO}	30			V	I _C =1mA
Emitter-Collector Breakdown Voltage	V(BR) _{ECO}	5			V	I _E =100 μ A
Collector-Emitter Dark Current	I _{CEO}			100	nA	V _{CE} =10V
COUPLER						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}			0.4	V	I _C =0.2mA I _F =20mA
On State Collector Current	I _{c(ON)}	0.4			mA	V _{CE} =5V I _F =20mA
Response Time	Rise Time	t _r	3	15	μS	V _{CE} =5V, I _c =2mA R _L =100Ω
	Fall Time	t _f	4	20		

TYPICAL ELECTRICAL / OPTICAL CHARACTERISTICS CURVES

(25 Ambient Temperature Unless Otherwise Noted)

Fig.1 Power Dissipation vs. Ambient Temperature

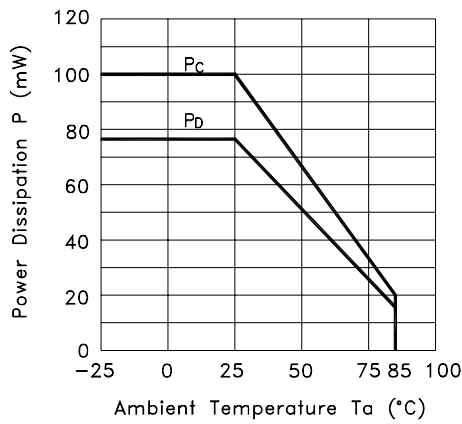


Fig.2 Forward Current vs. Forward Voltage

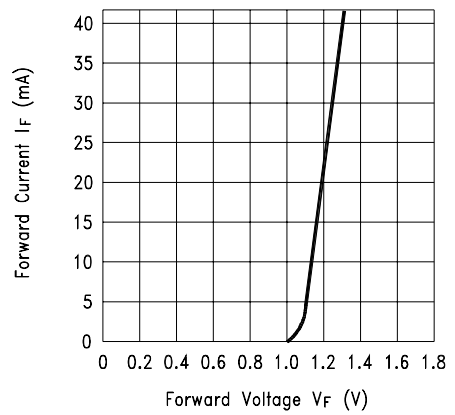


Fig.3 Collector Current vs. Collector-emitter Voltage

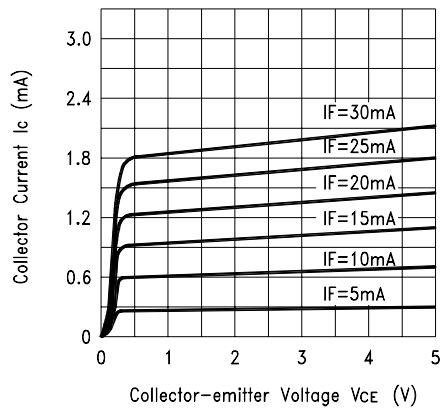
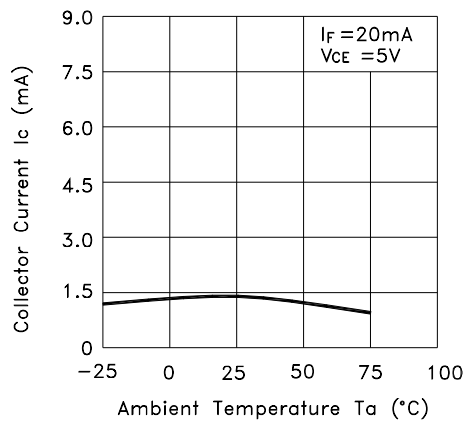


Fig.4 Collector Current vs. Ambient Temperature



TYPICAL ELECTRICAL / OPTICAL CHARACTERISTICS CURVES

(25 Ambient Temperature Unless Otherwise Noted)

Fig.5 Collector-emitter Saturation Voltage vs. Ambient Temperature

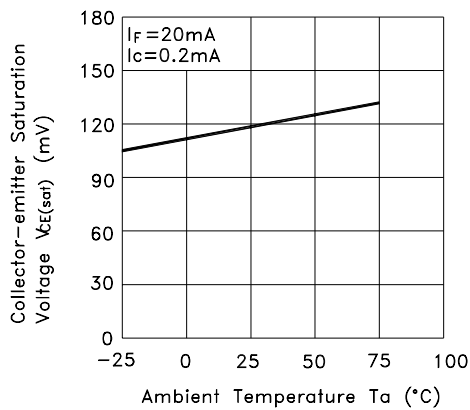
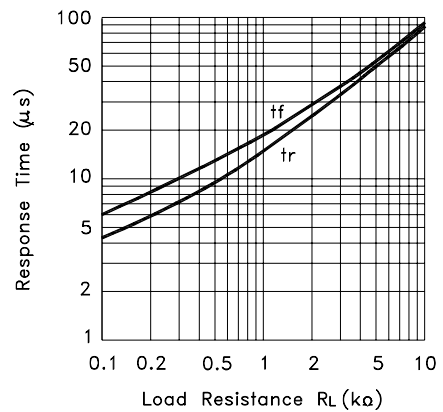


Fig.6 Response Time vs. Load Resistance



Test Circuit for Response Time

